

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	7	tsai near ching-tien.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:26
2	BRS	L2	6164	(oxide) near15 (silicon) near15 (poly)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:27
3	BRS	L3	8133	(oxide) near15 (silicon) near15 (polysilicon) near15 (substrate or wafer)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:28

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	0	(oxide) near15 (silicon) near15 (micro near polysilicon) near15 (substrate or wafer)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:28
5	BRS	L5	2	(oxide) near15 (silicon) near15 (crystalline near polysilicon) near15 (substrate or wafer)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:29
6	BRS	L6	3456	(oxide) near15 (silicon) near15 (amorphous) near15 (substrate or wafer)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:30

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	75	(oxide) near15 (silicon) near15 (amorphous) near15 (substrate or wafer) near25 (poly)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:45
8	BRS	L8	3106	(silicon) near5 (microcrystalline)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:45
9	BRS	L9	7	(silicon). near5 (microcrystalline near poly)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:46

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L11	2	(silicon) near5 (microcrystalline near polysilicon) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:47
11	BRS	L10	52	(silicon) near5 (microcrystalline near polysilicon)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:55
12	BRS	L12	0	(silicon) near5 (microcrystalline near polysilicon) near15 (furnace)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:49

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	0	(silicon) near5 (microcrystalline near polysilicon) near15 (temperature)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:49
14	BRS	L14	836	(polysilicon near floating) near15 (oxide)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:56
15	BRS	L15	1	(polysilicon near floating) near15 (oxide) near15 (seed or microcrystalline)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 13:57

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	2	(polysilicon near floating) near15 (oxide) near15 (amorphous)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 14:02
17	BRS	L17	0	(polysilicon near floating) near15 (oxide) near15 (amorphous) near15 (crystalline)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 14:02
18	BRS	L18	0	(polysilicon near floating) near15 (oxide) near15 (amorphous) near15 (control)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 2 14:02

	U	1	Document ID	Title	Current OR
1	X		US 20030121542 A1	Method for producing a solar module with thin-film solar cells which are series-connected in an integrated manner and solar modules produced according to the method, especially using concentrator modules	136/244
2	X		US 20030094892 A1	Field emission display cathode assembly	313/495
3	X		US 20030072009 A1	Tunable optical instruments	356/519
4			US 6509686 B1	Field emission display cathode assembly with gate buffer layer	313/495
5			US 6180975 B1	Depletion strap semiconductor memory device	257/306
6			US 6015323 A	Field emission display cathode assembly government rights	445/24

	U	1	Document ID	Title	Current OR
7			US 5133986 A	Plasma enhanced chemical vapor processing system using hollow cathode effect	427/569